

# 2SC1030

Silicon NPN Transistors

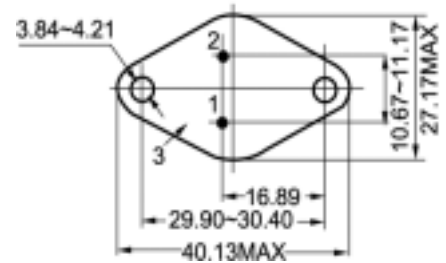
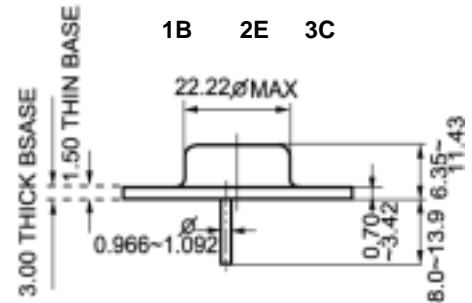


## ◆ Features

- With TO-3 package
- Low frequency power amplifications

## ◆ Absolute Maximum Ratings Tc=25°C

SYMBOL	PARAMETER	RATING	UNIT
V <sub>CBO</sub>	Collector to base voltage	150	V
V <sub>CEO</sub>	Collector to emitter voltage	80	V
V <sub>EBO</sub>	Emitter to base voltage	6	V
I <sub>C</sub>	Collector current-Continuous	6	A
P <sub>D</sub>	Total Power Dissipation@TC=25°C	50	W
T <sub>j</sub>	Junction temperature	200	°C
T <sub>stg</sub>	Storage temperature	-55~200	°C



TO-3

## ◆ Electrical Characteristics Tc=25°C

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V <sub>CEO</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> =0.2A; I <sub>B</sub> =0	80			V
V <sub>CER</sub>	Collector-Emitter Sustaining Voltage					
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> =30V; I <sub>B</sub> =0			2.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> =6V; I <sub>C</sub> =0			1.0	mA
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> =30V; I <sub>E</sub> =0			1.0	mA
V <sub>EBO</sub>	Base-emitter breakdown voltage					
V <sub>CE(sat-1)</sub>	Collector-emitter saturation voltages	I <sub>C</sub> =5.0A; I <sub>B</sub> =1.0A			1.5	V
V <sub>CE(sat-2)</sub>	Collector-emitter saturation voltages					
V <sub>CE(sat-3)</sub>	Collector-emitter saturation voltages					
h <sub>FE-1</sub>	Forward current transfer ratio	I <sub>C</sub> =1A; V <sub>CE</sub> =5V	35		200	
h <sub>FE-2</sub>	Forward current transfer ratio	I <sub>C</sub> =5A; V <sub>CE</sub> =5V	22			
h <sub>FE-3</sub>	Forward current transfer ratio					
V <sub>BE(on)</sub>	Base-emitter On voltages					
f <sub>T</sub>	Current Gain-Bandwidth Product	I <sub>C</sub> =1A; V <sub>CE</sub> =5V		10		MHz
h <sub>fe</sub>	Small-Signal Current Gain					